

MH185 Hall-effect sensor is a temperature stable, stress-resistant sensor. Superior high-temperature performance is made possible through a dynamic offset cancellation that utilizes chopper-stabilization. This method reduces the offset voltage normally caused by device over molding, temperature dependencies, and thermal stress.

MH185 includes the following on a single silicon chip: voltage regulator, Hall voltage generator, small-signal amplifier, chopper stabilization, Schmitt trigger, and open drain output. Advanced DMOS wafer fabrication processing is used to take advantage of low-voltage requirements, component matching, very low input-offset errors, and small component geometries.

This device requires the presence of both south and north polarity magnetic fields for operation. In the presence of a south polarity field of sufficient strength, the device output sensor on, and only switches off when a north polarity field of sufficient strength is present.

MH185 is rated for operation between the ambient temperatures  $-40^{\circ}\text{C}$  and  $85^{\circ}\text{C}$  for the E temperature range, and  $-40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$  for the K temperature range. The package style available provide magnetically optimized solutions for most applications. Package SO is an SOT-23, a miniature low-profile surface-mount package.

Packages is Halogen Free standard and which have been verified by third party lab.


### ***Features and Benefits***

- DMOS Hall IC Technology
- Chopper stabilized amplifier stage.
- Optimized for BLDC motor applications.
- Reliable and low shifting on high Temp condition.
- Switching offset compensation at typically 69kHz
- Good ESD Protection.
- 100% tested at  $125^{\circ}\text{C}$  for K.
- Custom sensitivity / Temperature selection are available.
- Reverse bias protection on power supply pin.
- RoHS compliant 2011/65/EU and Halogen Free

### ***Applications***

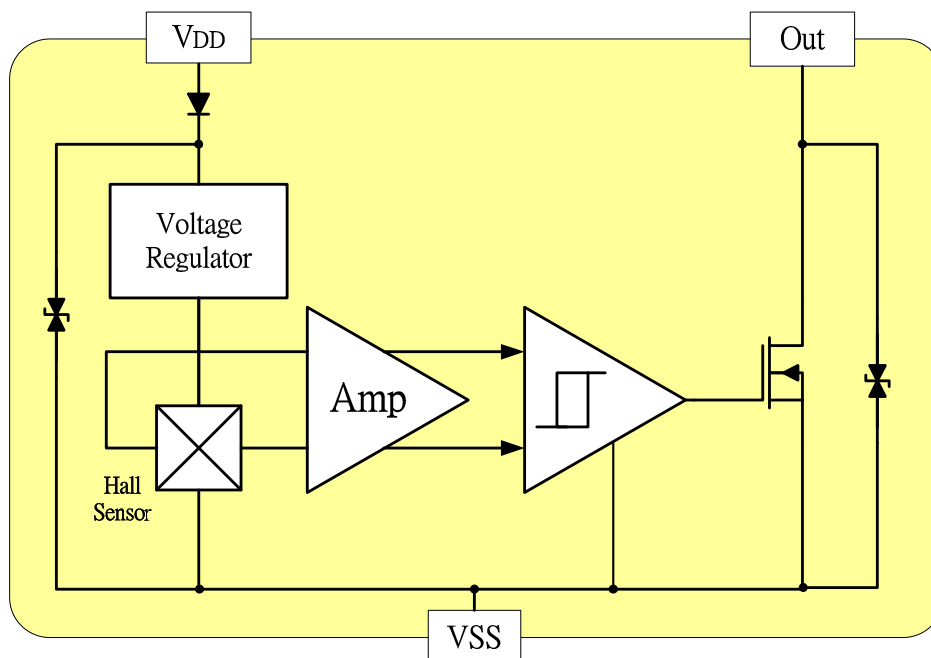
- High temperature Fan motor
- 3 phase BLDC motor application
- Speed sensing
- Position sensing
- Current sensing
- Revolution counting
- Solid-State Switch
- Linear Position Detection
- Angular Position Detection
- Proximity Detection
- High ESD Capability

### Ordering Information

	<p><b>Company Name and Product Category</b> MH:MST Hall Effect/MP:MST Power MOSFET</p> <p><b>Part number</b> 181,182,183,184,185,248,249,276,477,381,381F,381R,382..... If part # is just 3 digits, the forth digit will be omitted.</p> <p><b>Temperature range</b> E: 85 °C, I: 105 °C, K: 125 °C, L: 150 °C</p> <p><b>Package type</b> UA:TO-92S,VK:TO-92S(4pin),VF:TO-92S(5pin),SO:SOT-23, SQ:QFN-3,ST:TSOT-23,SN:SOT-553,SF:SOT-89(5pin)</p> <p><b>Sorting</b> <math>\alpha</math>, <math>\beta</math>, Blank.....</p>
<p>Sorting Code</p> <p>Package type</p> <p>Temperature Code</p> <p>Part number</p> <p>Company Name and product Category</p>	

Part No.	Temperature Suffix	Package Type
MH185KSO	K (-40°C to + 125°C)	SO (SOT-23)

### Functional Diagram



### Absolute Maximum Ratings At ( $T_a=25^{\circ}\text{C}$ )

Characteristics	Values	Unit	
Supply voltage, ( $V_{DD}$ )	28	V	
Output Voltage, ( $V_{out}$ )	28	V	
Reverse Voltage, ( $V_{DD} / V_{out}$ )	-0.3	V	
Output current, ( $I_{SINK}$ )	25	mA	
Operating Temperature Range, ( $T_A$ )	“E” Class	-40 ~ +85	$^{\circ}\text{C}$
	“K” Class	-40 ~ +125	$^{\circ}\text{C}$
Storage temperature range, ( $T_S$ )	-65 to +150	$^{\circ}\text{C}$	
Maximum Junction Temp, ( $T_J$ )	150	$^{\circ}\text{C}$	
Thermal Resistance	( $\theta_{JA}$ ) SO	543	$^{\circ}\text{C}/\text{W}$
	( $\theta_{JC}$ ) SO	410	$^{\circ}\text{C}/\text{W}$
Package Power Dissipation, ( $P_D$ ) SO	230	mW	

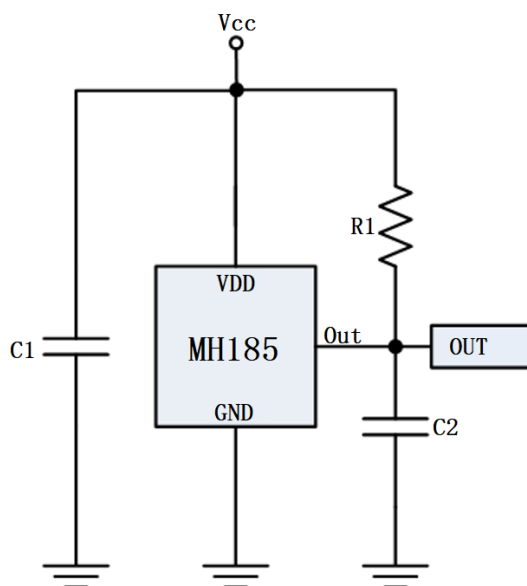
Note: Do not apply reverse voltage to  $V_{DD}$  and  $V_{OUT}$  Pin, It may be caused for Miss function or damaged device.

### Electrical Specifications

DC Operating Parameters :  $T_A=+25^{\circ}\text{C}$ ,  $V_{DD}=12\text{V}$

Parameters	Test Conditions	Min	Typ	Max	Units
Supply Voltage, ( $V_{DD}$ )	Operating	2.5		26	V
Supply Current, ( $I_{DD}$ )	$B < B_{OP}$		3.0	5.0	mA
Output Saturation Voltage, ( $V_{sat}$ )	$B > B_{OP}$			400.0	mV
Output Leakage Current, ( $I_{off}$ )	$I_{OFF} B < B_{RP}$ , $V_{OUT} = 12\text{V}$			10.0	$\mu\text{A}$
Output Rise Time, ( $T_R$ )	$R_L=1.1\text{K}\Omega$ , $C_L=20\text{pF}$			0.45	$\mu\text{S}$
Output Fall Time, ( $T_F$ )	$R_L=820\Omega$ ; $C_L=20\text{pF}$			0.45	$\mu\text{S}$
Electro-Static Discharge	HMB	4			KV
Operate Point, ( $B_{OP}$ )	SO	5		60	GS
Release Point, ( $B_{RP}$ )	SO	-60		-5	GS
Hysteresis, ( $B_{HYS}$ )	$ B_{OP} - B_{RP} $		60		GS

### Typical application circuit



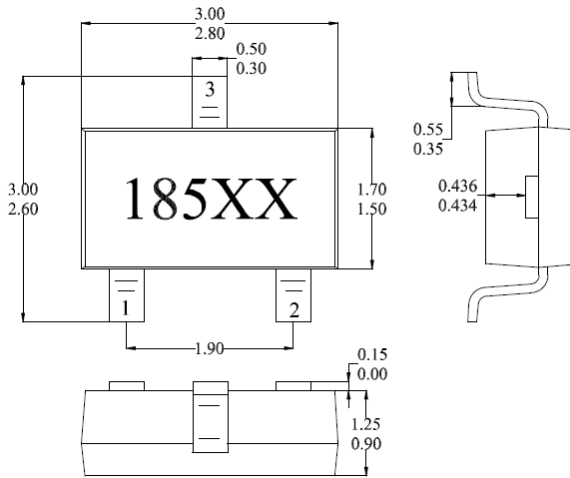
$C1 : 10\text{nF}$

$C2 : 1\text{nF}$

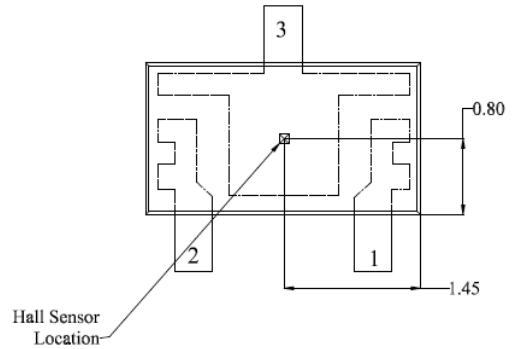
$R1 : 1\text{K}\Omega$

**Sensor Location, Package Dimension and Marking**

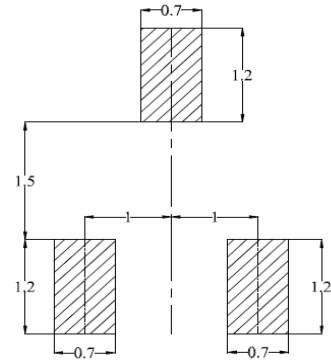
**SO Package  
(Top View)**



**Hall Plate Chip Location  
(Bottom view)**



**(For reference only) Land Pattern**



**NOTES:**

1. PINOUT (See Top View at left :)  
 Pin 1  $V_{DD}$   
 Pin 2 Output  
 Pin 3 GND
2. Controlling dimension: mm
3. Lead thickness after solder plating will be 0.254mm maximum